L Number	Hits	Search Text	DB	Time stamp
-	0	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/11/08 11:01
-	883	438/197.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:38
_	0	438/197.ccls. and "silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:45
_	106	"silicon germanium oxide"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:37
	21	"silicon germanium oxide" and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	17	"silicon germanium oxide" and epitaxial and deposition	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
_	15	"silicon germanium oxide" and epitaxial and deposition and gate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	14	"silicon germanium oxide" and epitaxial and deposition and gate and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:40
-	6	(("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:43
-	0	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 10:44
-	1	((("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	0	(("6200867") or ("6313505") or ("6594293")).PN. or ((2002/0182815) or (2003/0025163)).CCLS.) and (silicon with germanium) and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	102	438/197.ccls. and "silicon germanium"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
_	99	438/197.ccls. and "silicon germanium" and oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
-	48	438/197.ccls. and "silicon germanium" and oxide and epitaxial	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
	13	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14
_	12	438/197.ccls. and "silicon germanium" and oxide and (epitaxial with deposition) and remov\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/14 11:00

_	3.5	CH = 2.7.4 Feb. Grammard.m. Administration H	IICDAM.	2004/00/14
-	35	"silicon germanium deposition"	USPAT; US-PGPUB;	2004/09/14
		·	EPO; JPO;	11:01
			DERWENT	
1	20	"silicon germanium deposition" and	USPAT;	2004/09/14
-	20	epitaxial	US-PGPUB;	11:01
		epitaniai	EPO; JPO;	11.01
		·	DERWENT	
_	20	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4	US-PGPUB;	11:01
			EPO; JPO;	
		•	DERWENT	
_	8	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate	US-PGPUB;	11:02
			EPO; JPO;	
			DERWENT	, , ,
-	6	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:02
İ			EPO; JPO;	
	_	11 12 1	DERWENT USPAT;	2004/09/14
-	5	"silicon germanium deposition" and	USPAT; US-PGPUB;	11:02
1		epitaxial and remov\$4 and gate and etch\$4	EPO; JPO;	11:02
]	and transistor	DERWENT	
1_	0	"silicon germanium deposition" and	USPAT;	2004/09/14
-		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:03
		and transistor and protect\$4 and clean	EPO; JPO;	
		and clansistor and proceeds, and croan	DERWENT	
_	0	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:03
		and transistor and protect\$4 and ash\$4	EPO; JPO;	
		-	DERWENT	
_	2		USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:32
		and transistor and protect\$4	EPO; JPO;	
			DERWENT	
-	0	"silicon germanium deposition" and	USPAT;	2004/09/14
		epitaxial and remov\$4 and gate and etch\$4	US-PGPUB;	11:33
		and transistor and protect\$4 and (wash or	EPO; JPO; DERWENT	
		clean) "silicon germanium oxide" near9 gate and	USPAT;	2004/09/14
_	0	epitaxial	US-PGPUB;	11:38
		epicaniai	EPO; JPO;	
			DERWENT	
	2	"silicon germanium oxide" near9 gate	USPAT;	2004/09/14
	_	Dilloon golmaniam onla mode gare	US-PGPUB;	11:42
			EPO; JPO;	
			DERWENT	
-	658	"silicon germanium" near9 gate	USPAT;	2004/09/14
			US-PGPUB;	11:42
			EPO; JPO;	
		<u> </u>	DERWENT	0004/00/14
-	231		USPAT;	2004/09/14
		epitaxial	US-PGPUB;	11:42
			EPO; JPO; DERWENT	
	105	"silicon germanium" near9 gate and	USPAT;	2004/09/14
-	195	epitaxial and remov\$4	US-PGPUB;	11:46
		- ebicavial and temovia	EPO; JPO;	
			DERWENT	
_	9131	(oxide near9 gate) and epitaxial and	USPAT;	2004/09/14
		remov\$4	US-PGPUB;	11:46
		·	EPO; JPO;	<u> </u>
	1		DERWENT	
-	1307		USPAT;	2004/09/14
		remov\$4 and "silicon germanium"	US-PGPUB;	11:46
		'	EPO; JPO;	
			DERWENT	2004/00/14
-	1048		USPAT;	2004/09/14
		remov\$4 and "silicon germanium" and	US-PGPUB; EPO; JPO;	11:47
		pattern\$4	DERWENT	'
I	1		I NEVARIAT	L

			0000100101
	ear9 gate) and epitaxial and	USPAT;	2004/09/14
remov\$4	and "silicon germanium" and	US-PGPUB;	11:47
pattern\$	4 and oxidiz\$4	EPO; JPO;	
		DERWENT	
	ear9 gate) and epitaxial and	USPAT;	2004/09/14
	and "silicon germanium" and	US-PGPUB;	11:48
pattern\$	4 and oxidiz\$4 and (clean or	EPO; JPO;	!
wash)		DERWENT	į
- 12 (oxide n	ear9 gate) and epitaxial and	USPAT;	2004/09/14
	and "silicon germanium" and	US-PGPUB;	11:48
pattern\$	4 and oxidiz\$4 and (clean or	EPO; JPO;	
wash) an	d recess	DERWENT	ļ
- 12 (oxide n	ear9 gate) and epitaxial and	USPAT;	2004/09/14
remov\$4	and "silicon germanium" and	US-PGPUB;	11:48
pattern\$	4 and oxidiz\$4 and (clean or	EPO; JPO;	
	d recess and etch\$4	DERWENT	
	ear9 gate) and epitaxial and	USPAT;	2004/09/14
	and "silicon germanium" and	US-PGPUB;	11:49
	4 and oxidiz\$4 and (clean or	EPO; JPO;	
	d recess and etch\$4 and electrode	DERWENT	
	ear9 gate) and epitaxial and	USPAT;	2004/09/14
	and "silicon germanium" and	US-PGPUB;	11:49
	4 and oxidiz\$4 and (clean or	EPO; JPO;	11.32
	d recess and etch\$4 and electrode	DERWENT	
and diel		DEKWENI	[
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	ear9 gate) and epitaxial and	USPAT;	2004/09/14
	and "silicon germanium" and	US-PGPUB;	11:49
		EPO; JPO;	11.49
	4 and oxidiz\$4 and (clean or	DERWENT	
	d recess and etch\$4 and electrode	DEKMENT	
	ectric and protect\$4	Manam.	2004/11/03
- 109 "silicon	germanium oxide"	USPAT;	2004/11/03
		US-PGPUB;	12:51
		EPO; JPO;	
		DERWENT	2004/31/02
- 15 "silicon	germanium oxide" and gate and	USPAT;	2004/11/03
epitaxia	l and above and remov\$4	US-PGPUB;	12:54
		EPO; JPO;	
		DERWENT	0004/01/00
- 2836 dielectr	ic and electrode and protect\$4	USPAT;	2004/11/08
	\$4 and oxidiz\$4 and expos\$4 and	US-PGPUB;	11:51
	ductor or wafer or substrate) and	EPO; JPO;	
pattern\$	4 and (clean\$4 or wash\$4)	DERWENT	
- 3 dielectr	ic and electrode and protect\$4	USPAT;	2004/11/08
	\$4 and oxidiz\$4 and expos\$4 and	US-PGPUB;	11:52
	ductor or wafer or substrate) and	EPO; JPO;	1
	4 and (clean\$4 or wash\$4) and	DERWENT	
l ("silico	n germanium oxide" or SiGeO)		